

Micromachining using femtosecond laser pulses

1. Overview of femtosecond laser pulses
 - some acronyms
 - laser system
 - diagnostic tools
 - properties
2. Micromachining
 - modeling
 - short pulse ($< \text{ps}$) vs. long pulse ($> \text{ps}$)
 - animations
 - micromachining on dielectric
 - some results
3. Conclusions

1 femtosecond (fs) = 10^{-15} second = 0.3 μm in vacuum

1 attosecond (as) = 10^{-18} second = 0.3 nm in vacuum

Transform – limited – pulse

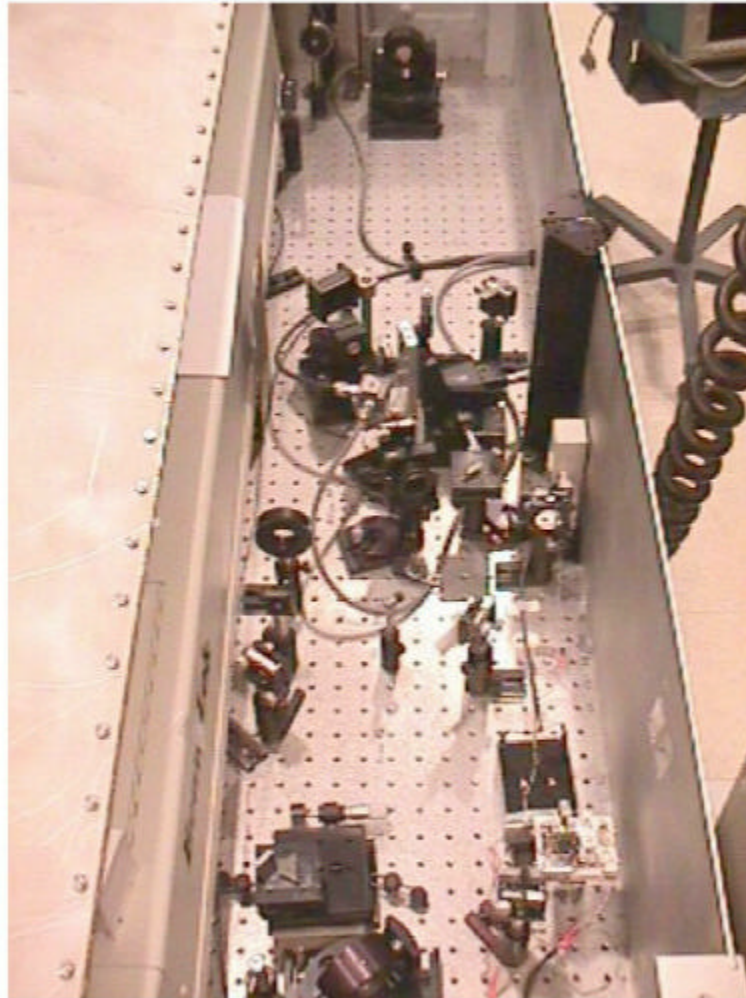
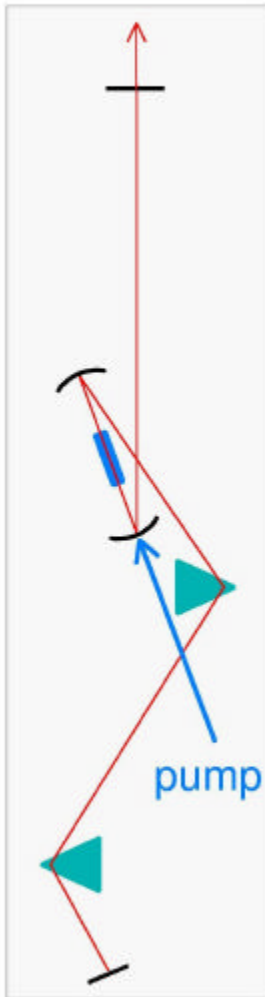
$$\Delta t \Delta E = h$$

$$\Delta t \text{ (fs)} \Delta \lambda \text{ (nm)} = \frac{4.4 \times 10^3}{3} \lambda^2 \text{ (}\mu\text{m)} \quad \text{Gaussian pulse}$$

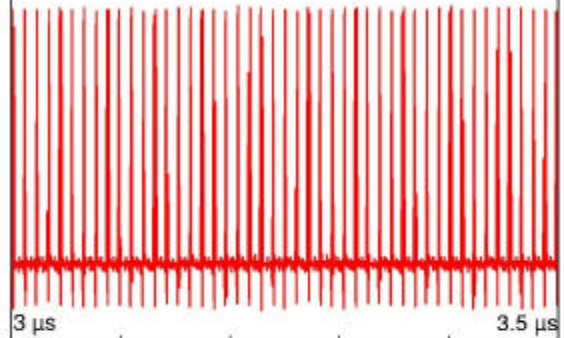
λ (nm)	E (eV)	Δt (fs)	$\Delta \lambda$ (nm)	$\Delta \nu$ (GHz)
800	1.55	100	9.4	4400
800	1.55	17	55	26,000
800	1.55	4	235	110,000
13.7	90	~ 0.65	-	-

* one optical cycle = 2.67 fs at 800 nm

Ti:sapphire laser oscillator



oscillator pulse train



100 MHz repetition rate

100 fs

800 nm (1.55 eV)

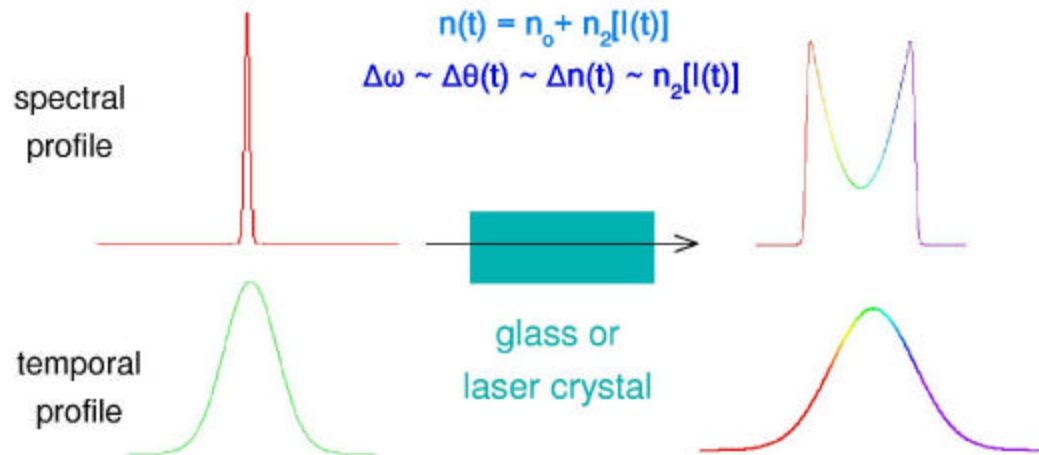
3 nJ/pulse (10^{10} photons)

30 kW/pulse

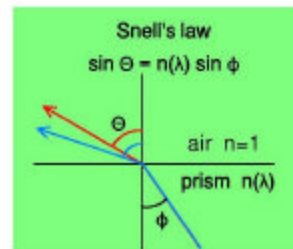
5×10^{12} Watts/cm²

Combined SPM and dispersion compensation - short pulse formation

Self-phase modulation - nonlinear effect

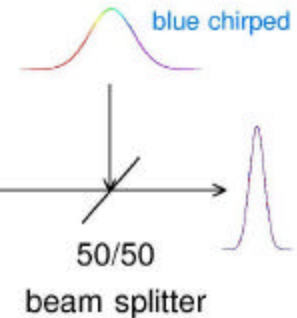


Prism pair
(dispersion compensation)



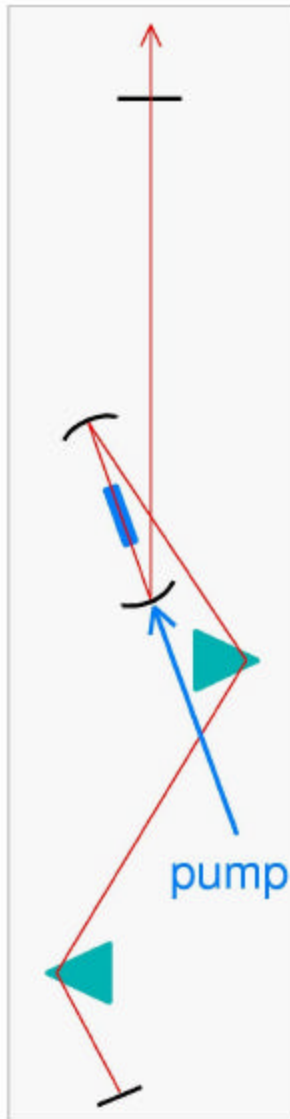
mirror

blue > red

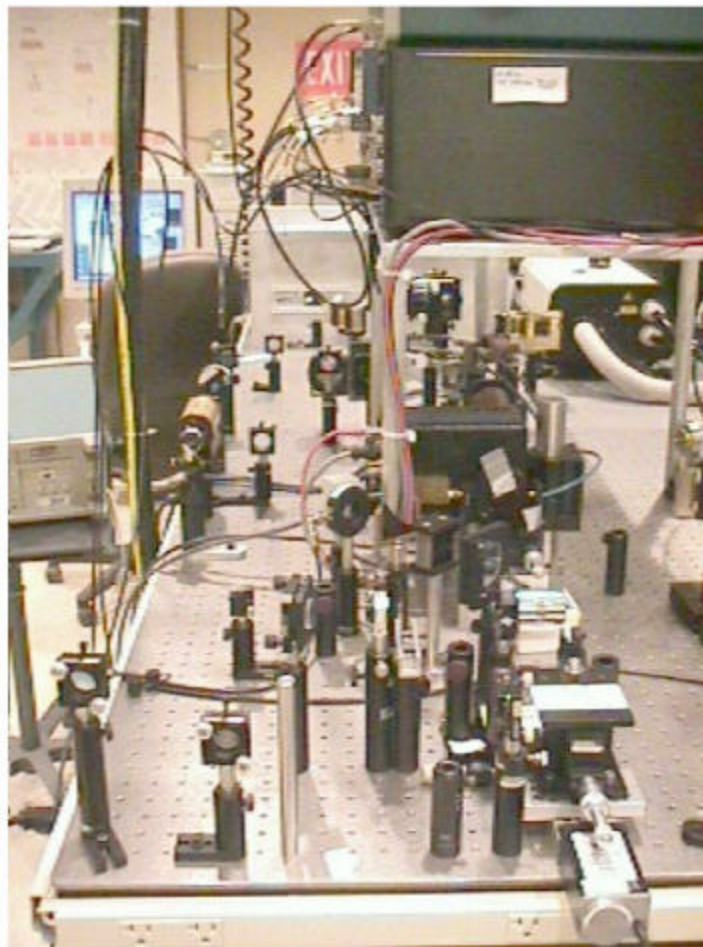
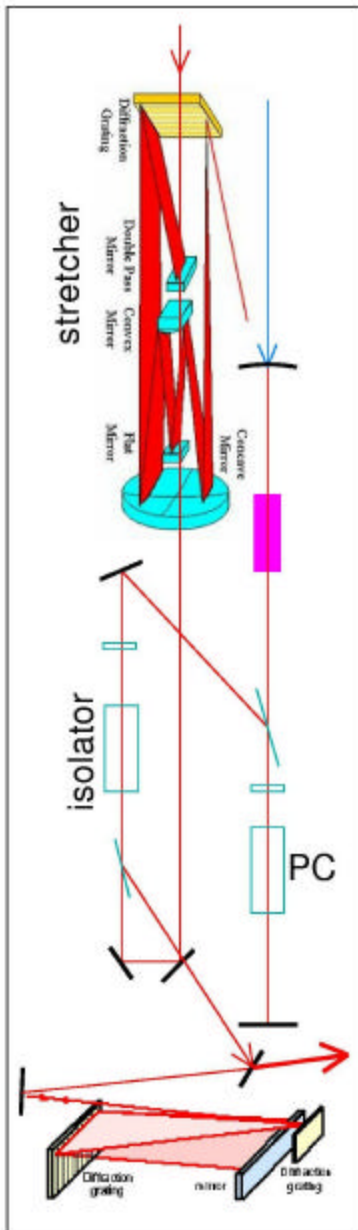


$$T(\omega) = \frac{d\phi}{d\omega} = T_0 = \text{constant}$$

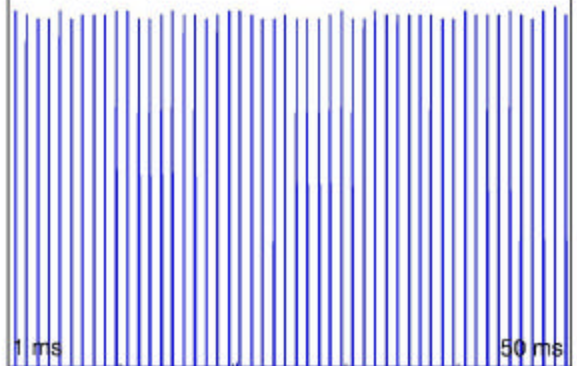
$$\phi(\omega) = \phi_0 + \phi_1(\omega - \omega_0) + \phi_2(\omega - \omega_0)^2 + \phi_3(\omega - \omega_0)^3 + \dots$$



Ti:sapphire laser amplifier



amplified pulse train



1 kHz repetition rate

200 fs

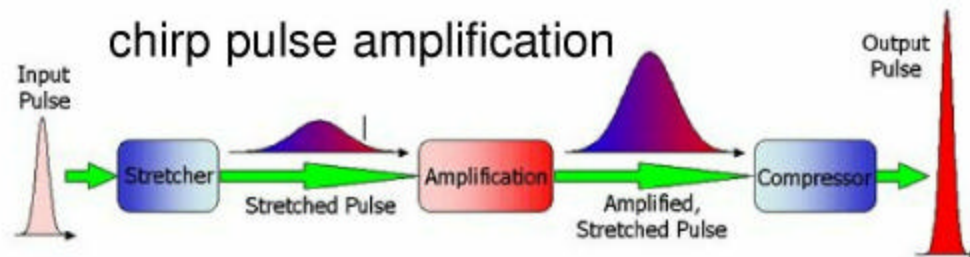
800 nm (1.55 eV)

0.8 mJ/pulse ($\sim 10^{15}$ photons)

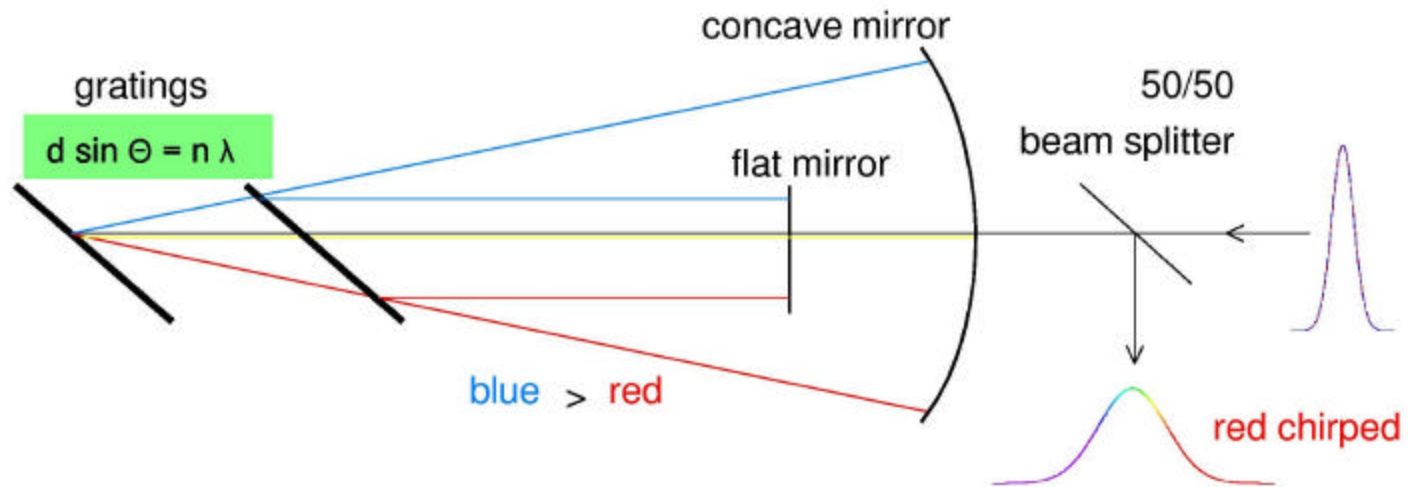
4 GW/pulse

4×10^{17} Watts/cm²

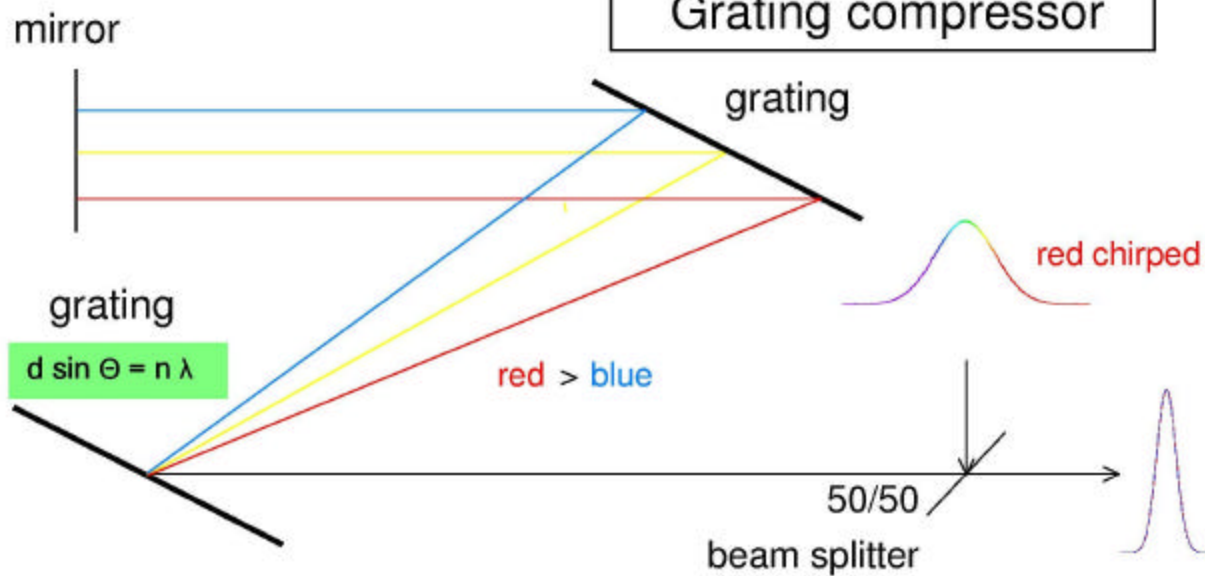
chirp pulse amplification



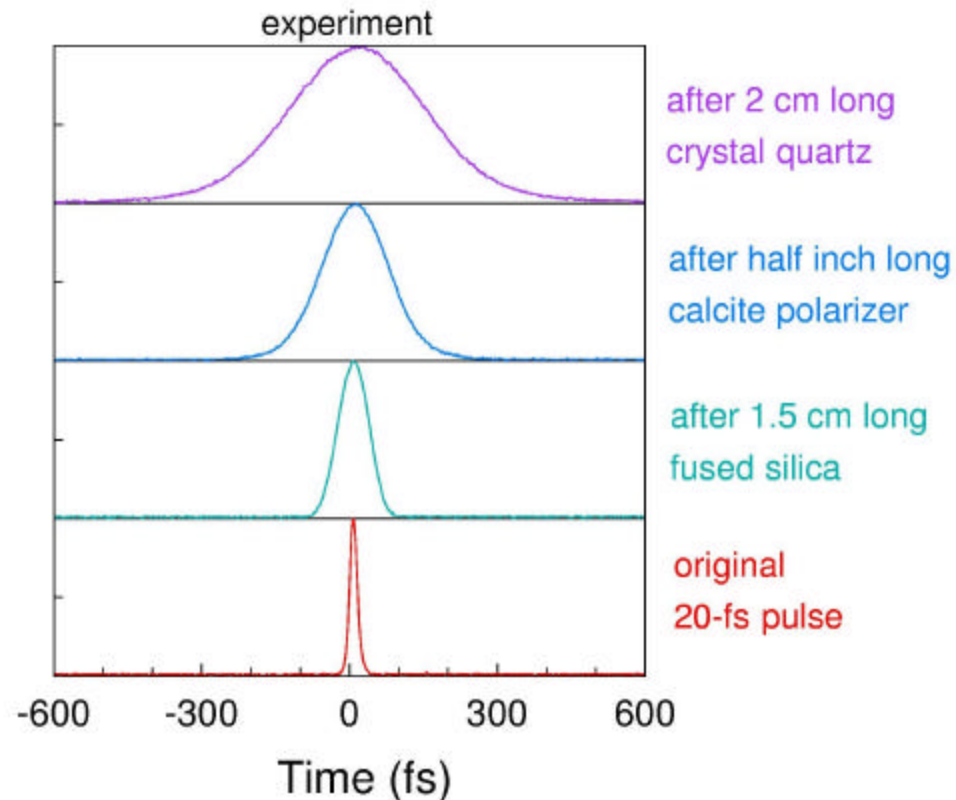
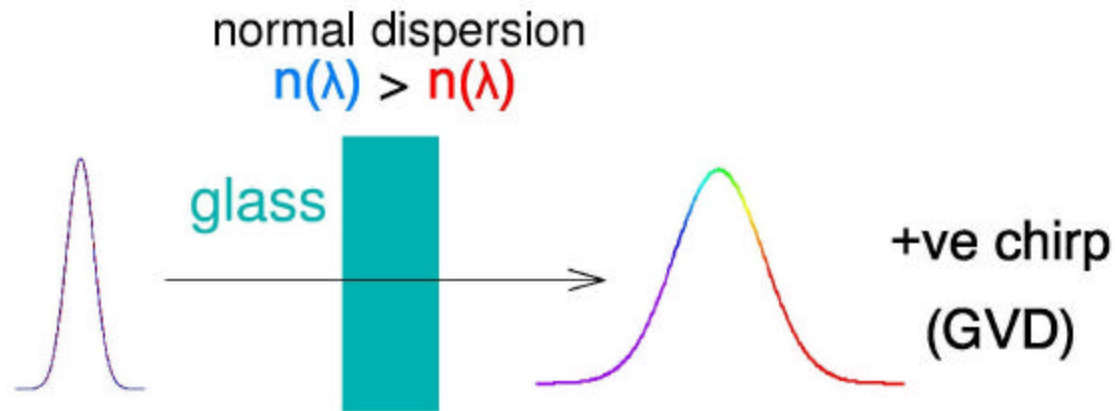
Pulse stretcher



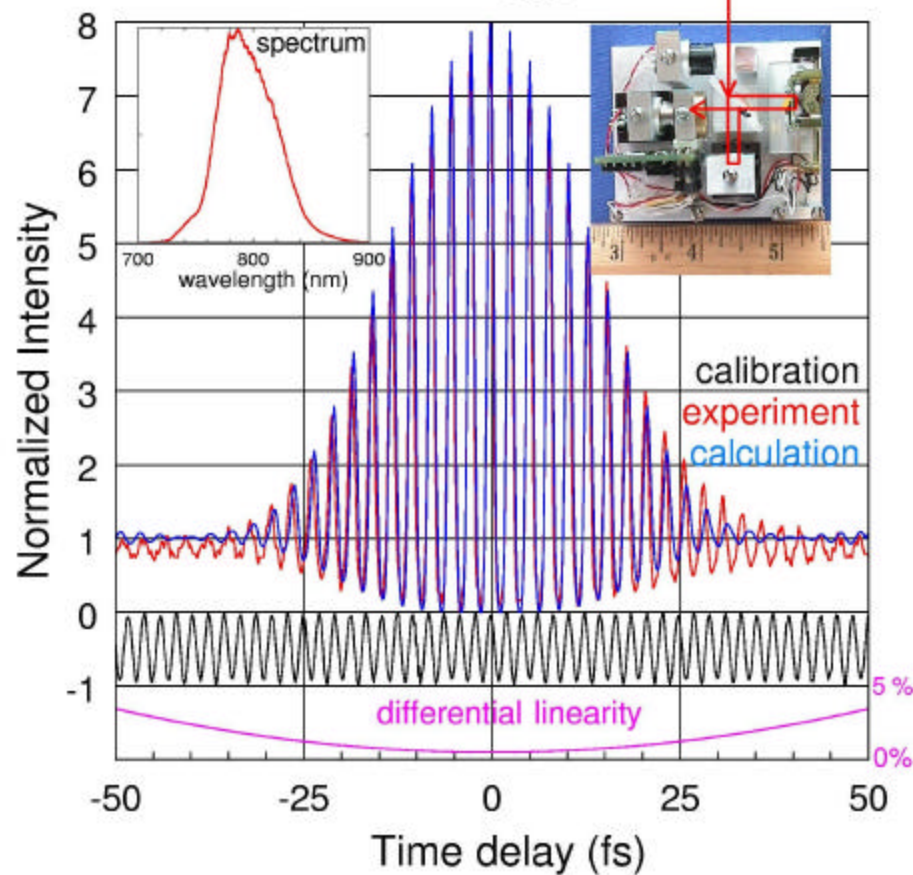
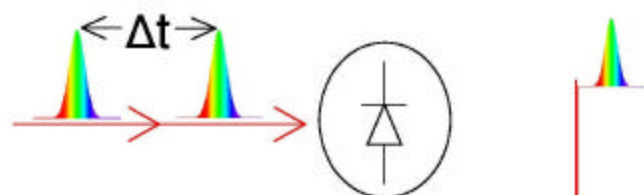
Grating compressor



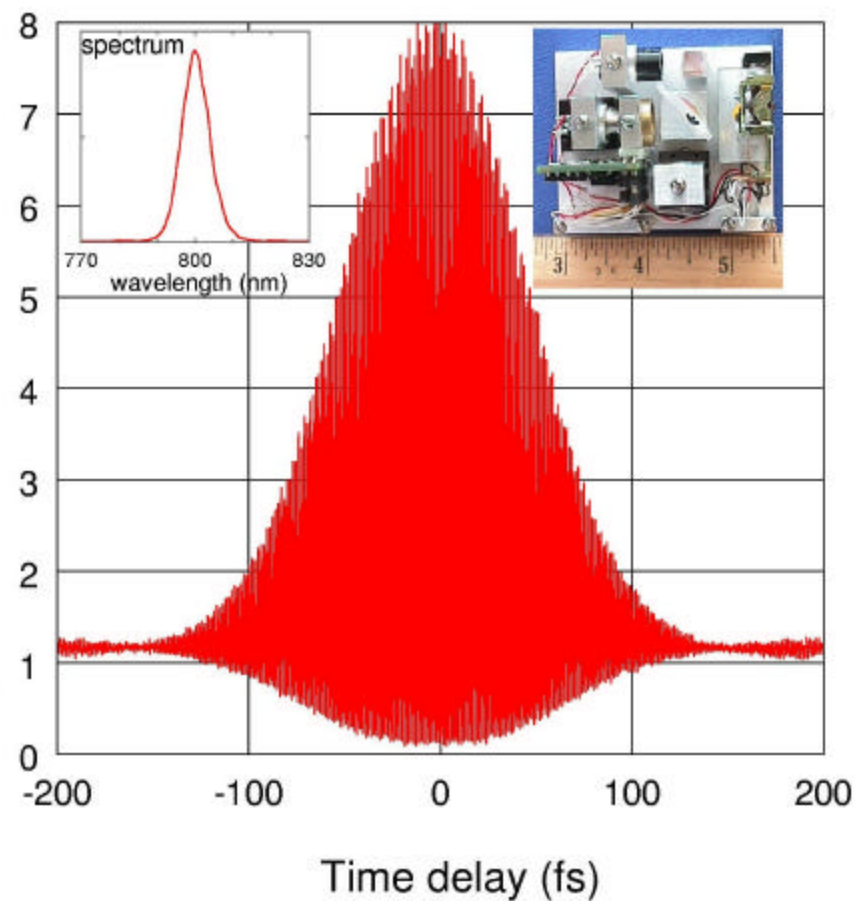
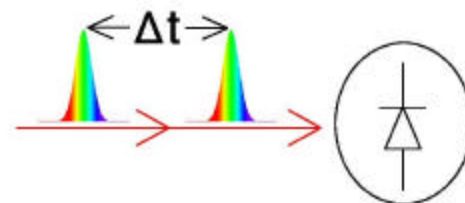
Group velocity dispersion (GVD) - linear effect

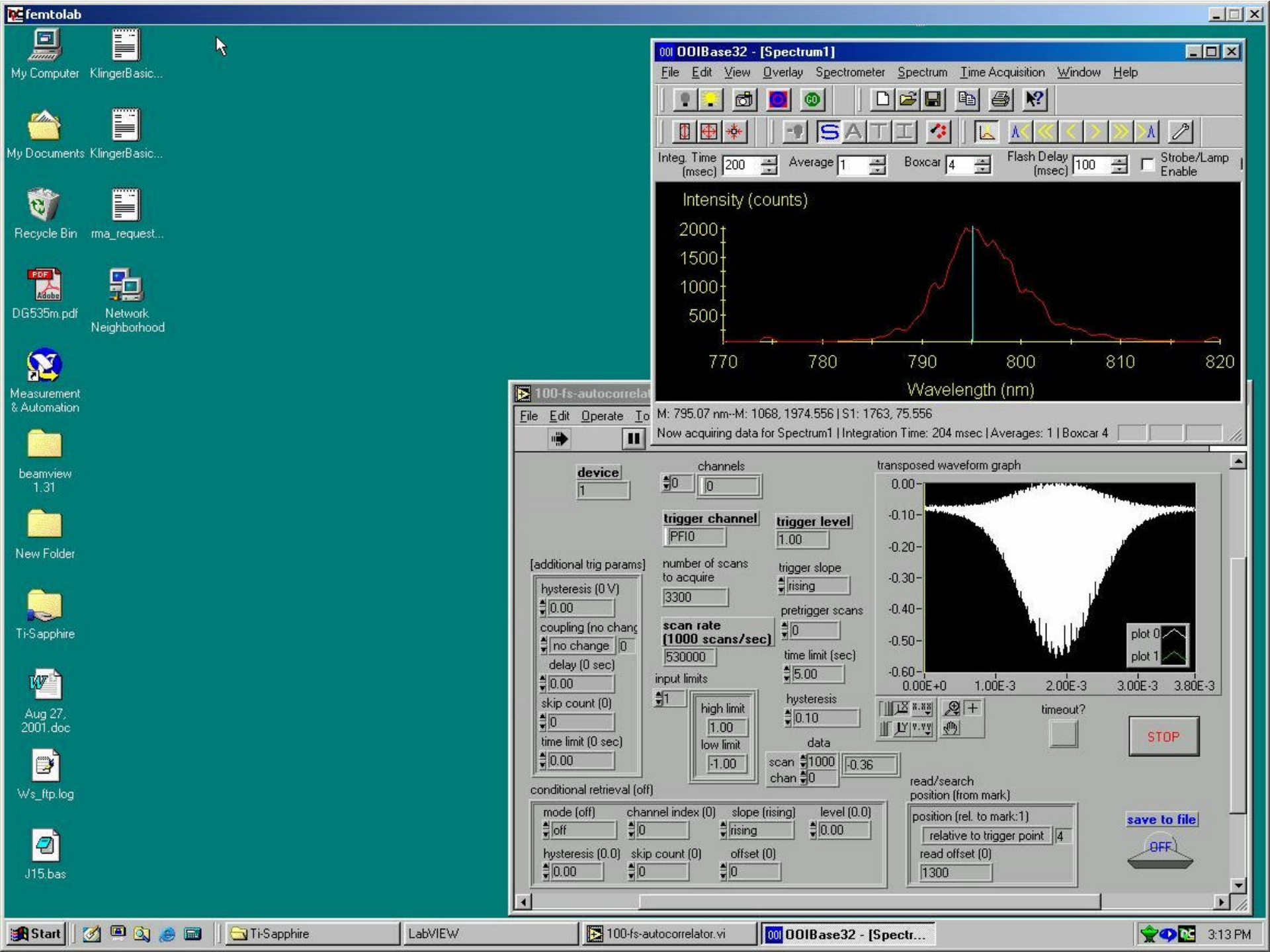


2-photon photoconductivity (17 fs pulse)

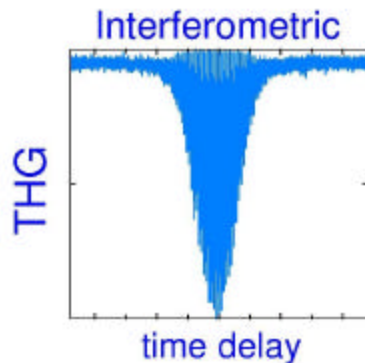
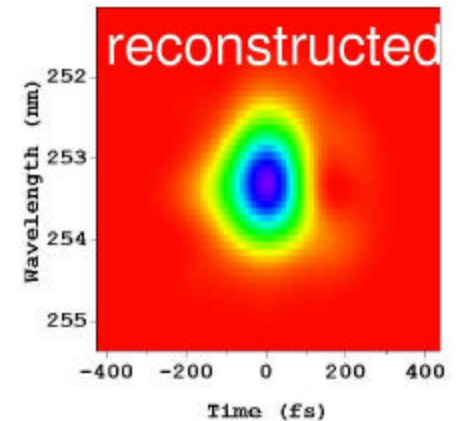
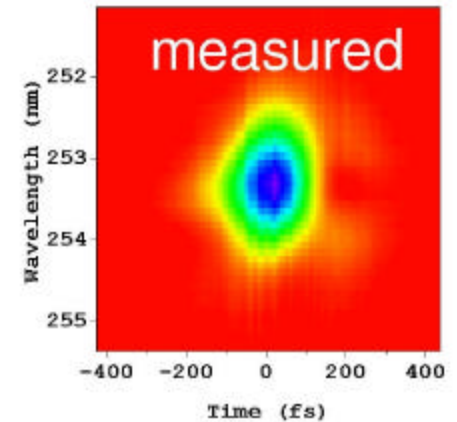
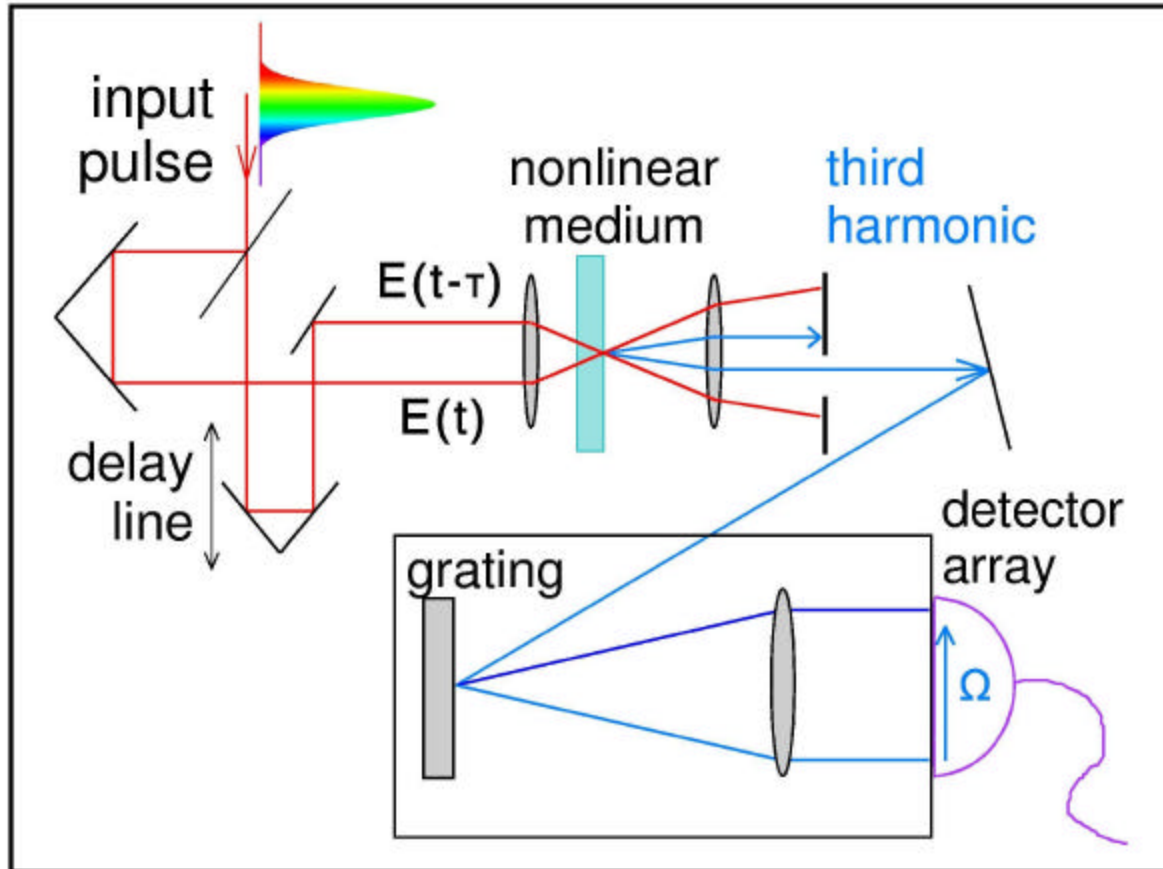


2-photon photoconductivity (100 fs pulse)



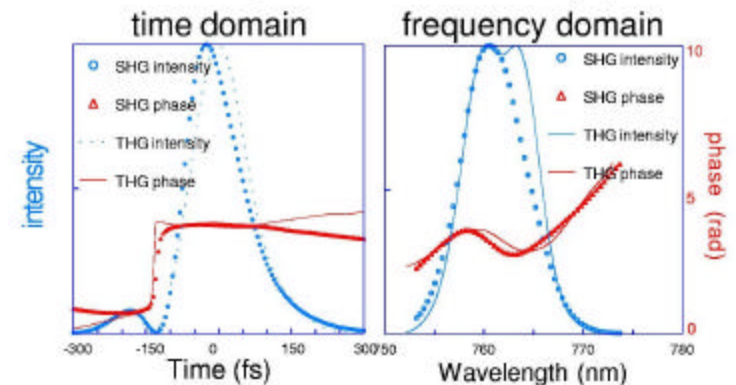


FROG - frequency-resolved optical gating - Third-harmonic generation



$$\mathbf{E} = E(t) e^{i\phi(t)}$$

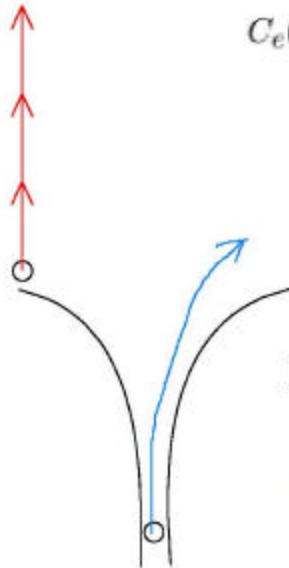
$$\omega = \omega(t) e^{i\theta(t)}$$



heat diffusion time \sim ns- μ s duration
 electron-phonon relaxation time \sim ps
 nonequilibrium temperatures

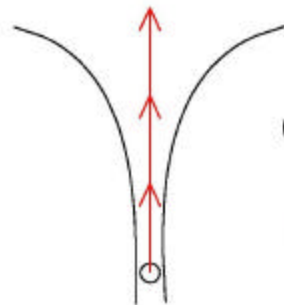
$$C_e(T_e) \frac{\partial T_e}{\partial t} = \kappa \Delta^2 T_e - G(T_e - T_l) + P_o(r, t)$$

$$C_l \frac{\partial T_l}{\partial t} = G(T_e - T_l)$$



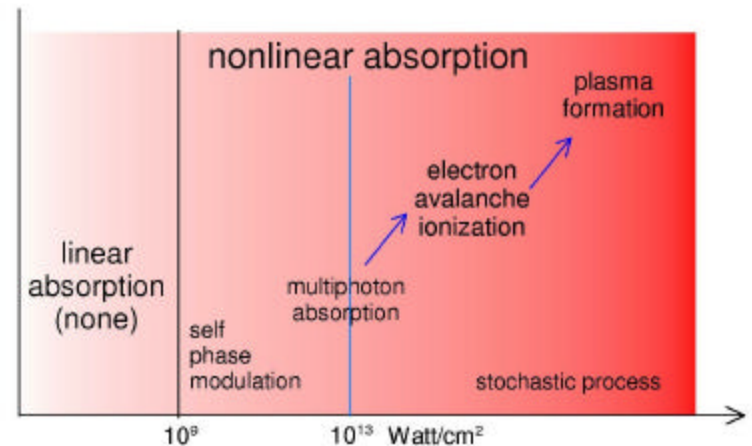
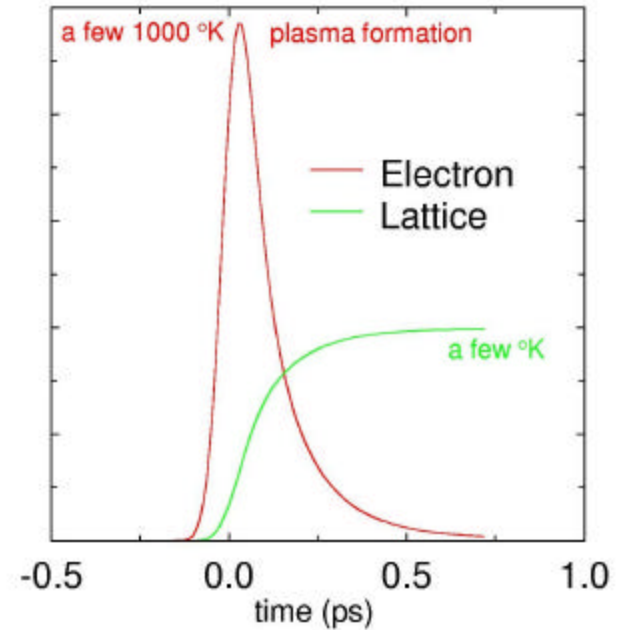
metals and opaque materials

avalanche ionization



dielectric materials

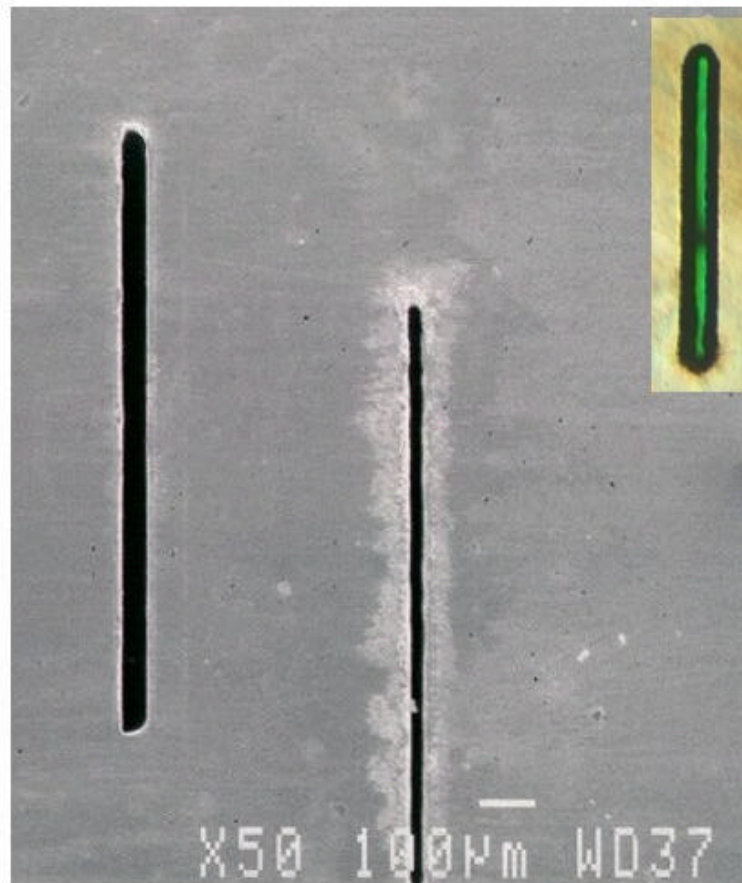
multiphoton absorption



- Animation of long pulses versus short pulses

[Animation Index File \(click here to open\)](#)

A channel machined in 1 mm thick INVAR, Nickel/Iron alloy under the same experimental conditions as the long pulse channel in Figure 4.1, but with ultrafast pulses. This channel was machined with 200 femtosecond pulses, 0.5 mJ energy per pulse. It is quite obvious that the channel machined with femtosecond pulses is cleaner than the sample machined with nanosecond pulses (place link to figure 4.1). Note also the absence of a recast layer. It is also clear that the machining process was more efficient – the channel is larger. The edges are straighter. Overall the quality of the micromachining is much higher.

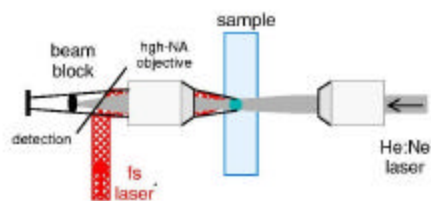
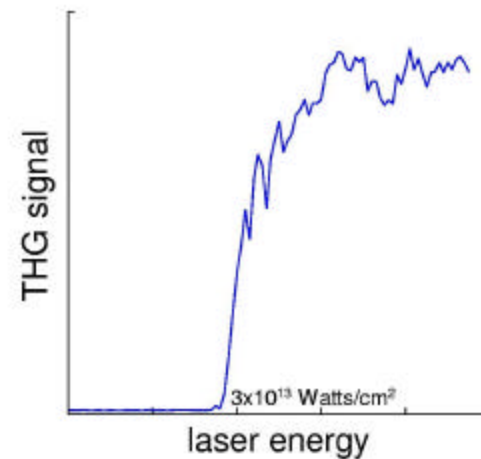
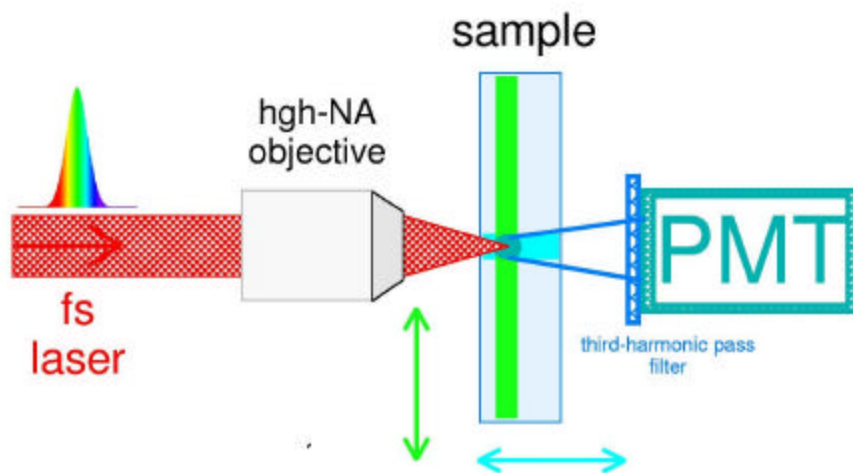
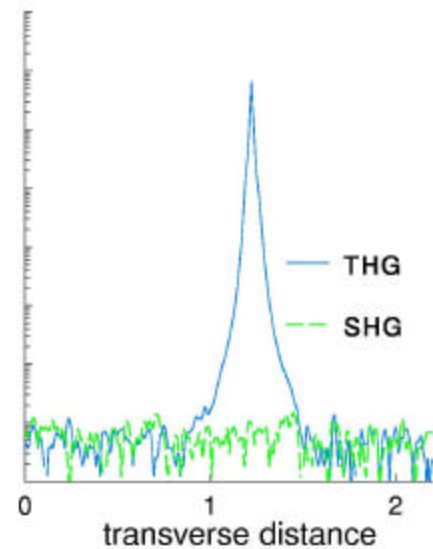
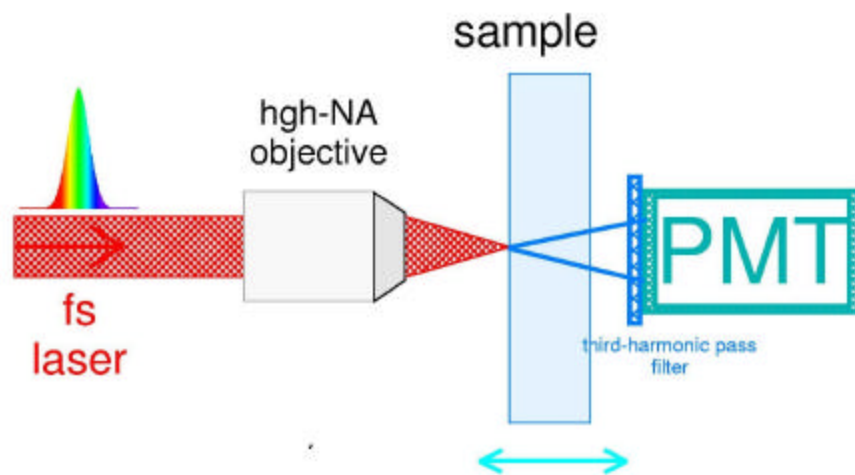


Source: Clark-MXR, Inc.

Figure 6.1: Channel machined in INVAR with ultrafast laser.

Process of Dielectric breakdown

- excitation of electron in conduction band by multi-photon (or impact) ionization
- heating of conduction band by free electron to form a critical density electron plasma
- continue absorption of laser energy by plasma
- plasma expands as a highly energetic gas
- heat diffusion is “frozen” during laser interaction, minimum energy is deposited to the lattice.
- process is precise and reproducible - a controlled damage





100 micron depth



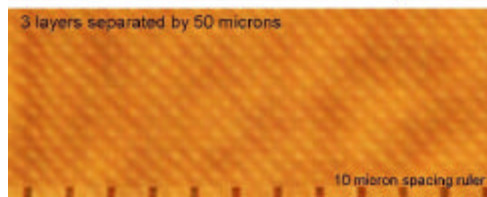
200 micron depth



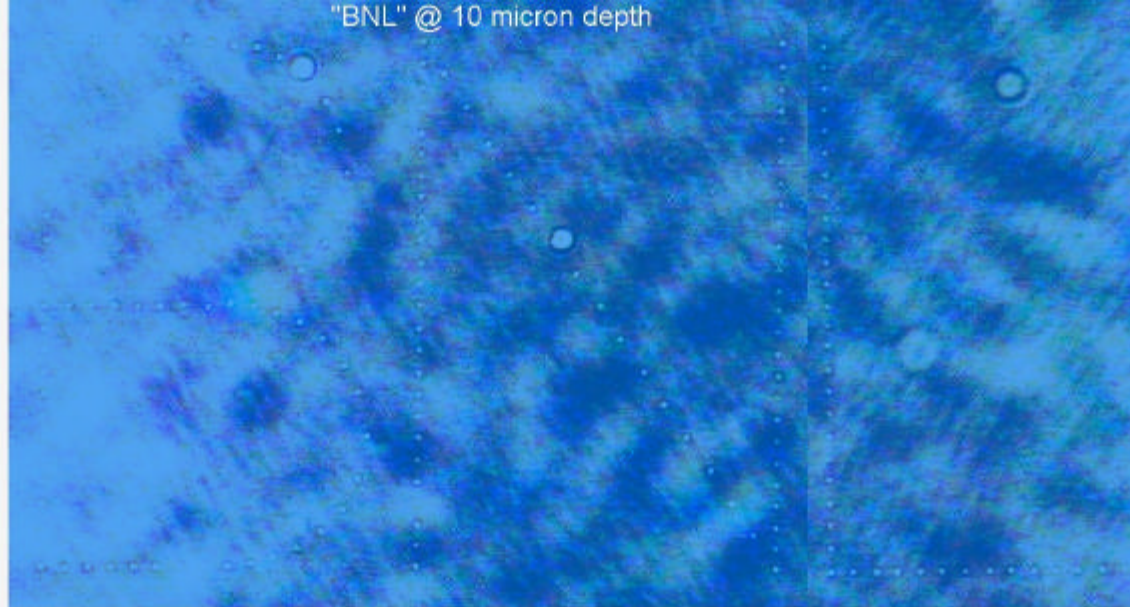
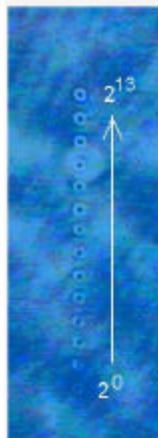
300 micron depth



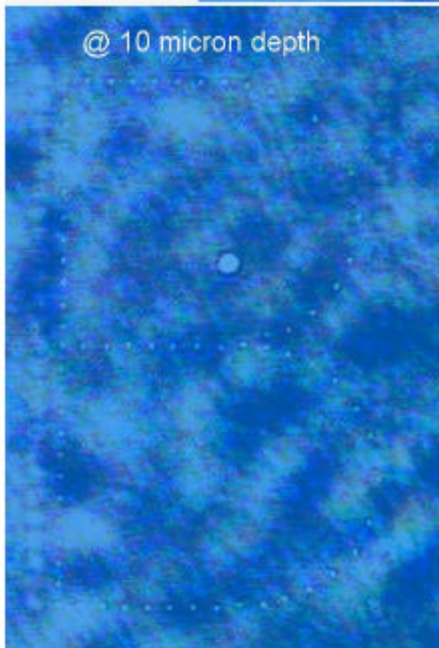
3 layers separated by 50 microns



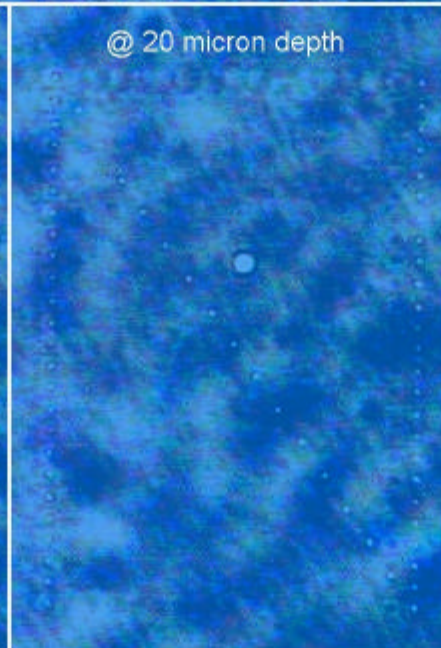
"BNL" @ 10 micron depth



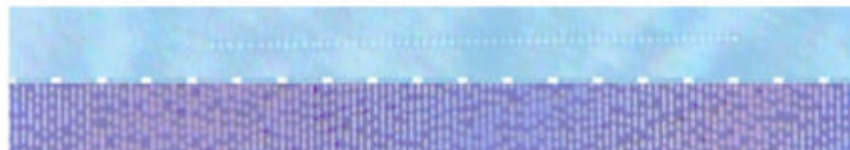
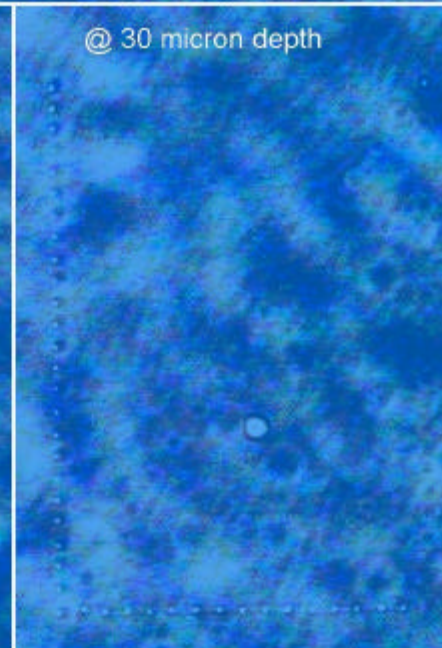
@ 10 micron depth



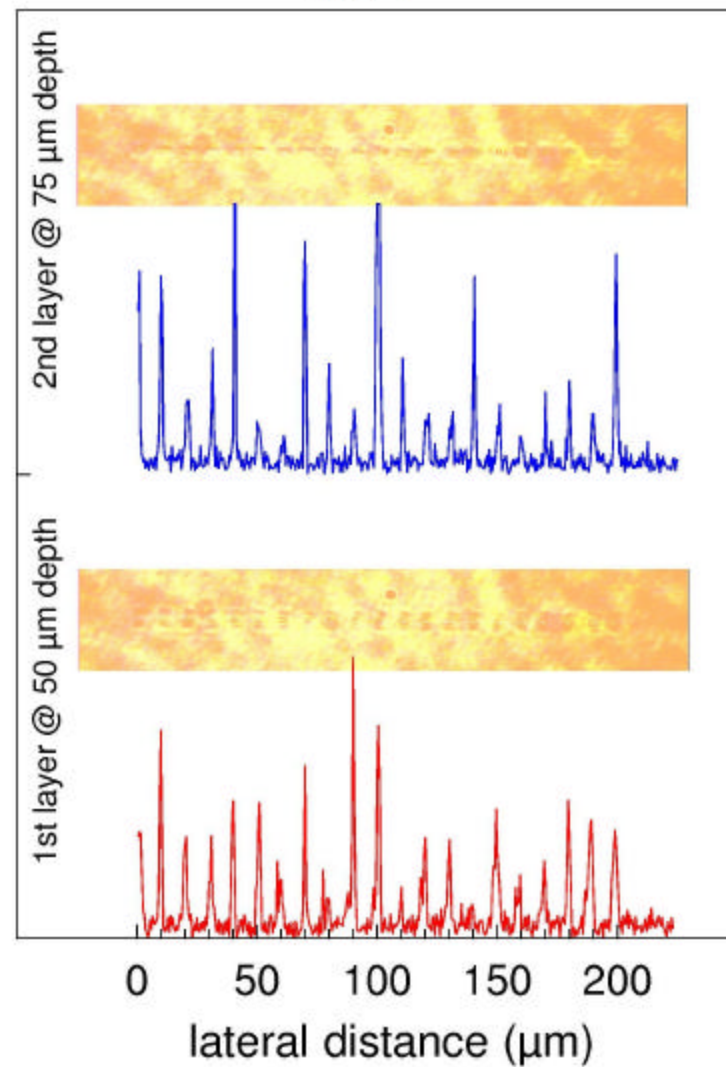
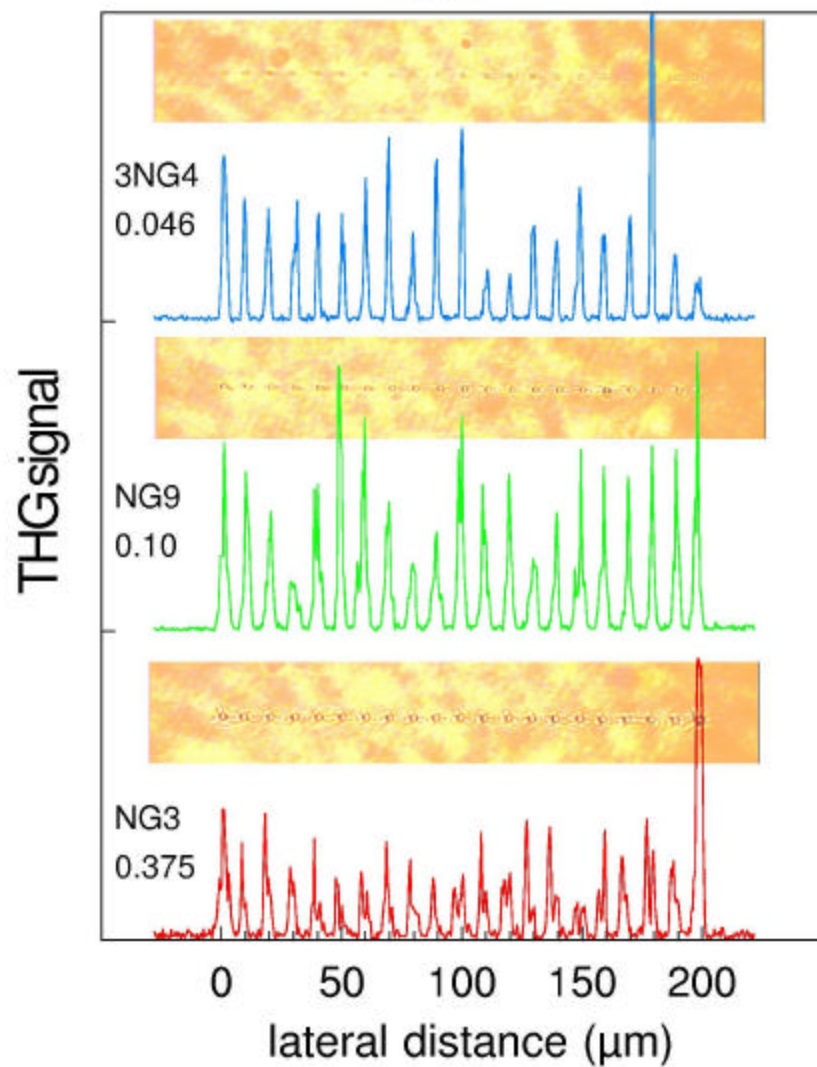
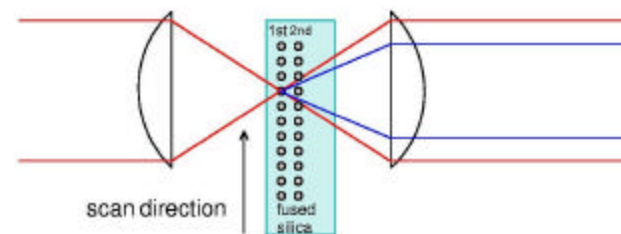
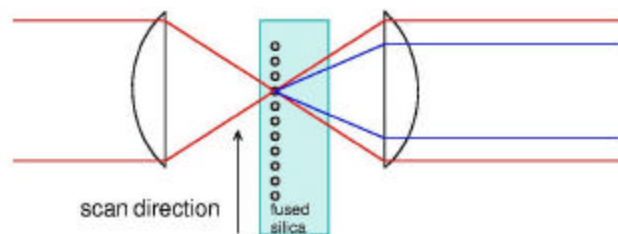
@ 20 micron depth

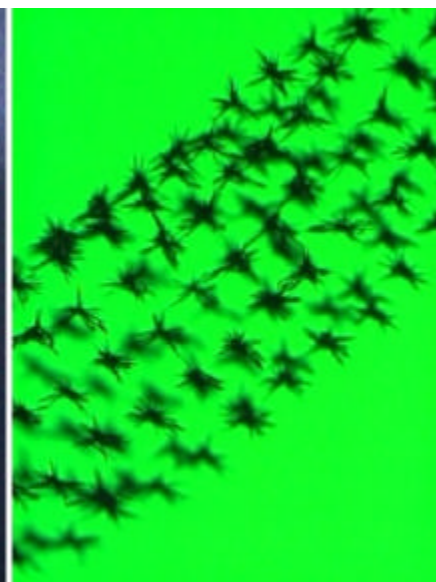


@ 30 micron depth



	650 MB CD	4.7 GB DVD	3-D dielectric
density	6.5 MB/cm ²	47 MB/cm ²	10 ⁵ - 10 ⁶ MB/cm ³
bit size	15 μm ² /bit	2 μm ² /bit	1 - 10 μm ³ /bit

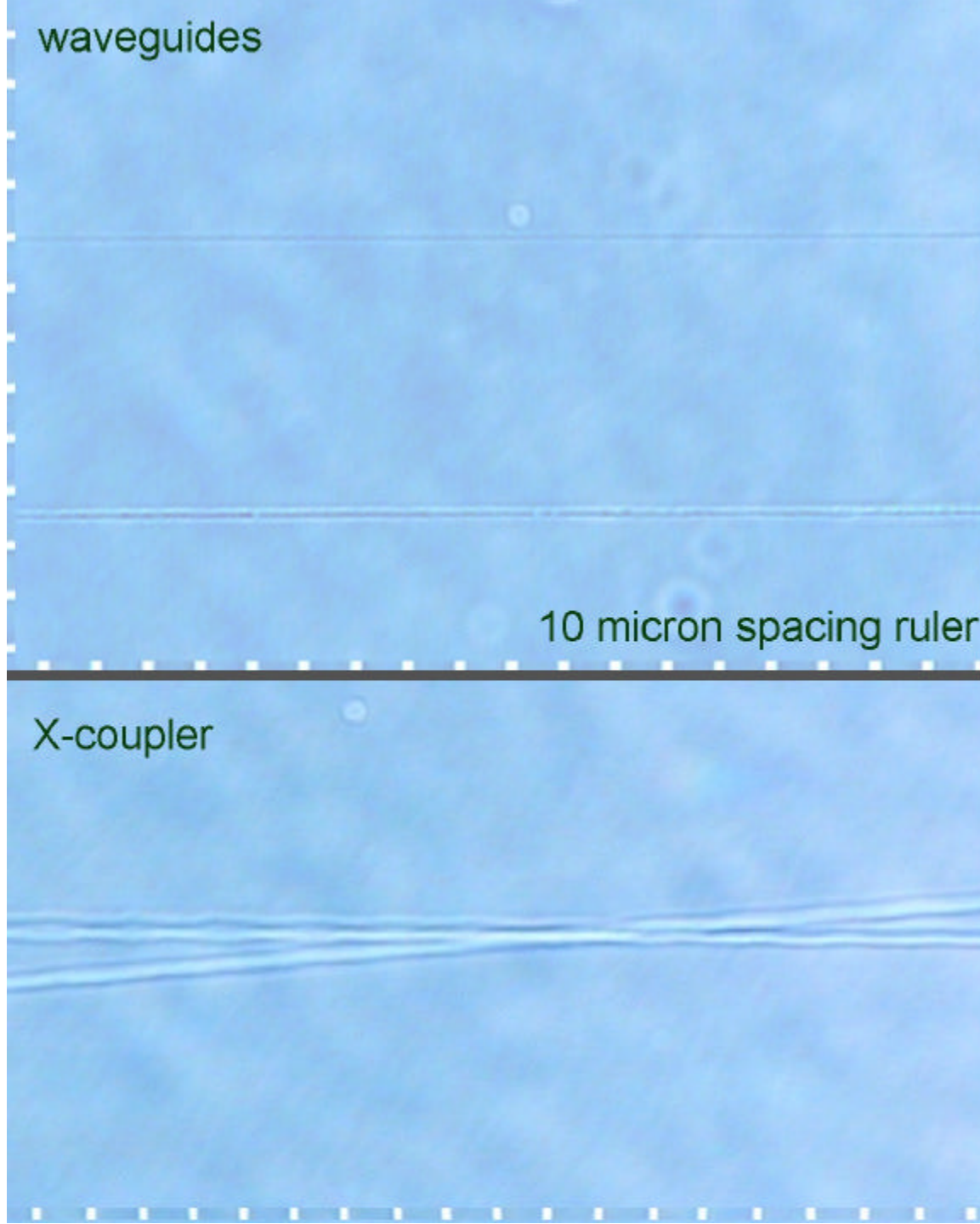


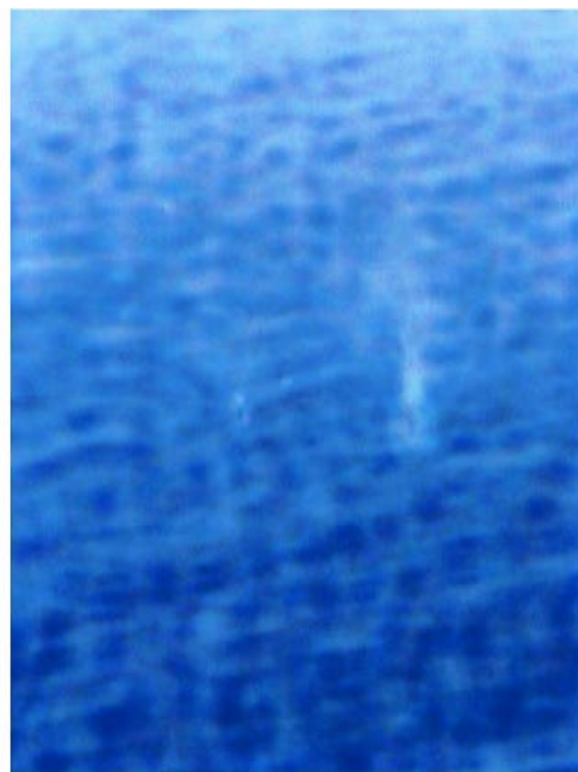
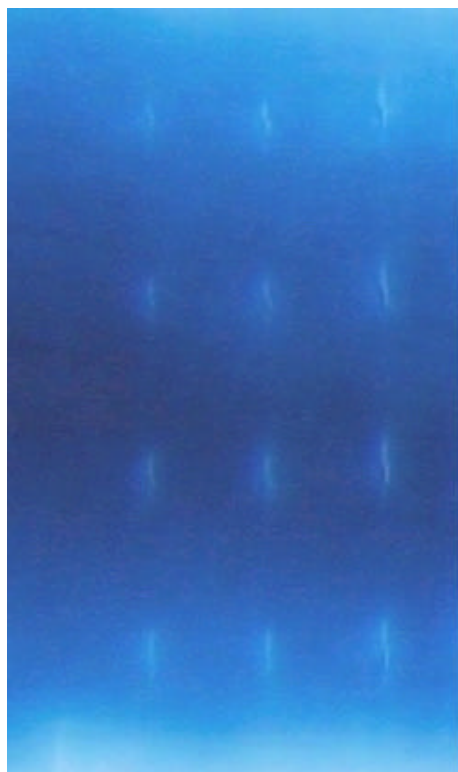


waveguides

10 micron spacing ruler

X-coupler





some laser machining parameters

pulse width	200 fs
spot size	1-2 μm diameter
power density	$\sim 8 \times 10^{13}$ Watts/cm ²
energy density	~ 16 Joule/cm ²
energy/pulse	160 nanoJoule/pulse
# of pulses	$10^3 - 10^4$
Δn	$10^{-3} - 10^{-4}$

$$E_{\text{th}} = \text{power threshold} = \frac{I_{\text{th}} \tau \lambda^2}{\pi(\text{NA})^2 + I_{\text{th}} \frac{\lambda}{P_{\text{cr}}}} = \sim 3 \times 10^{13} \text{ Watts/cm}^2$$

P_{cr} = critical power for self focusing

I_{th} = optical breakdown threshold

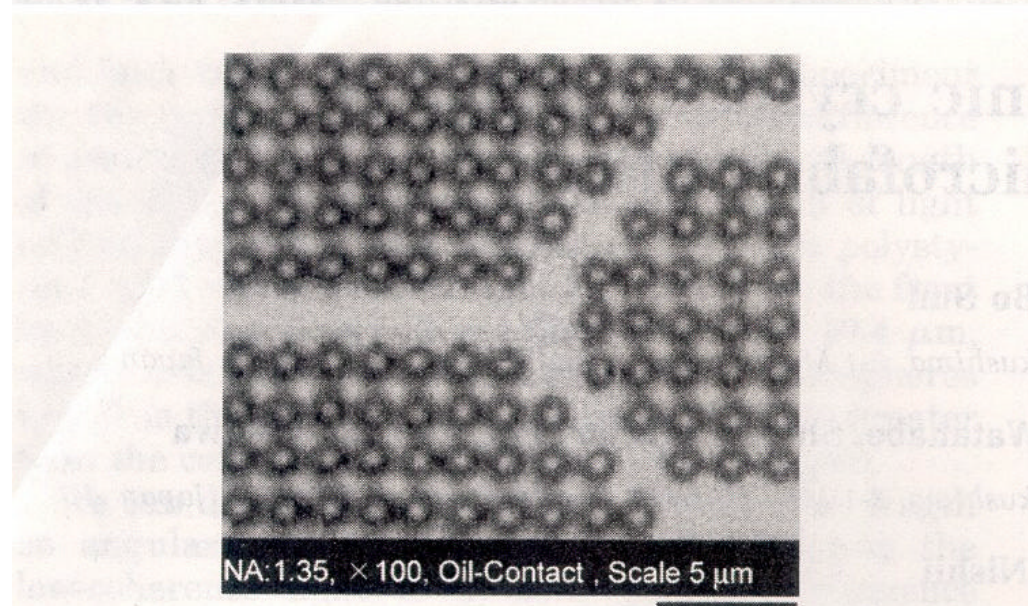
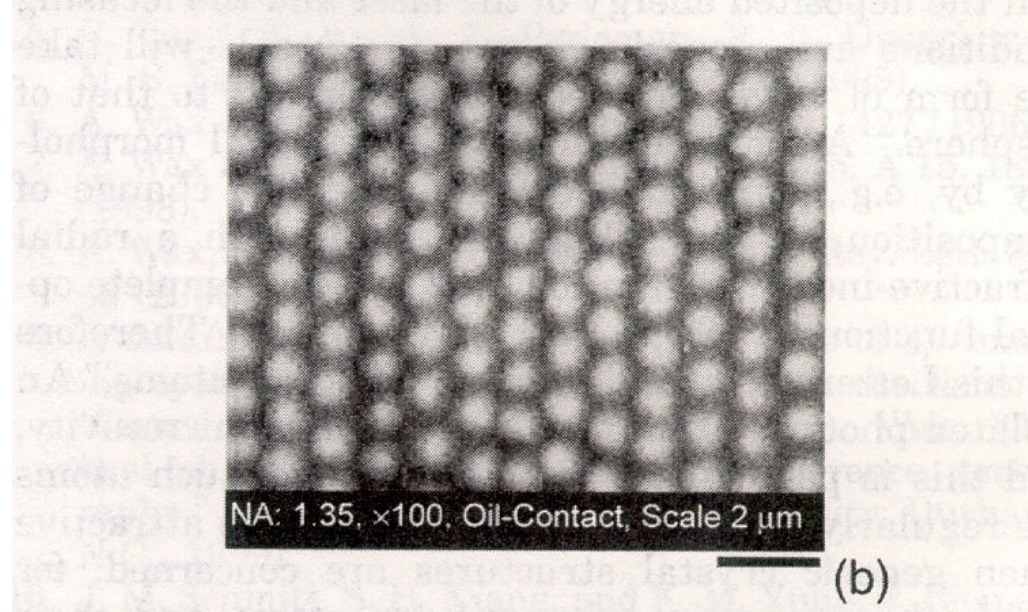
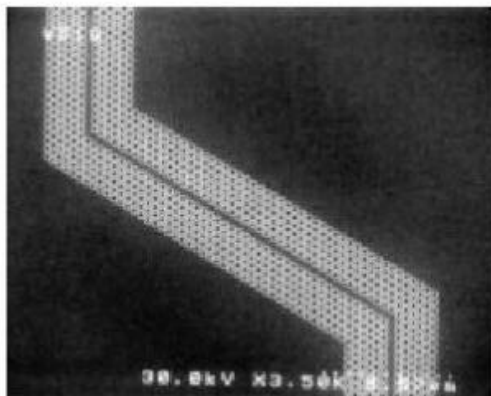
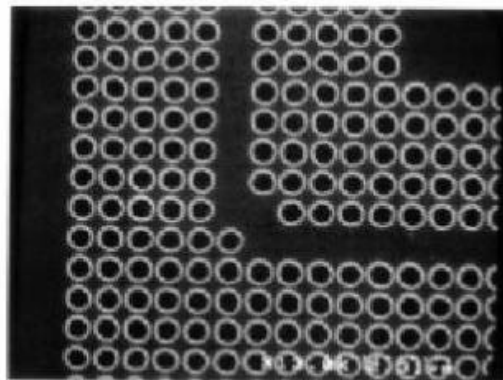


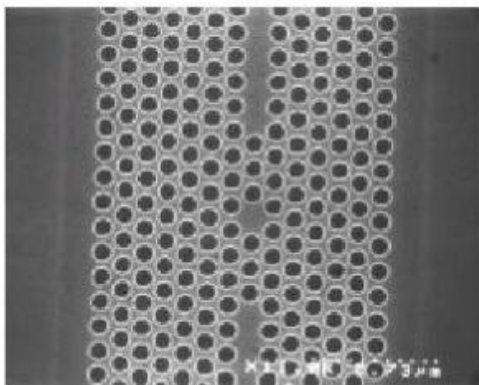
Fig. 1. (100) Plane of an sc photonic lattice in Ge-doped silica. The empty Y-shaped area consists of missing photonic atoms and functions as a microintegrated optical waveguide.



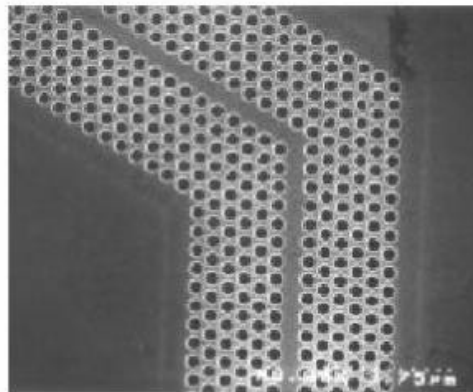
(a)



(a)

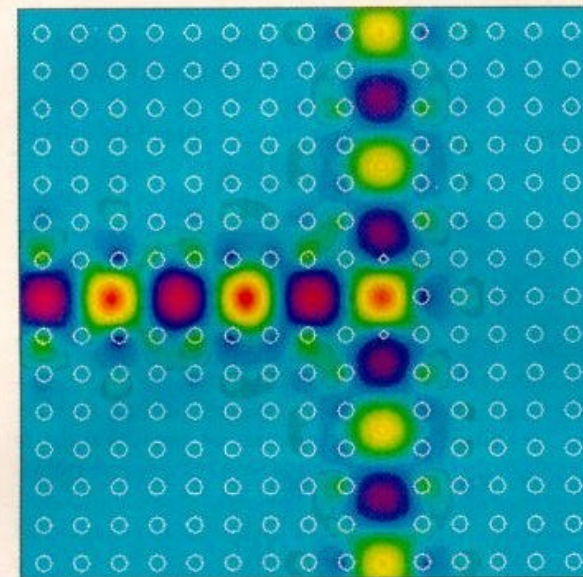


(b)



(b)

Fig. 8. (a) Waveguide with two 60° bends and 25 μm bend-to-bend spacing. (b) High- Q cavity filter formed by coupling single-defect cavity to the two waveguide sections.



-1.00 0.00 1.00

Figure 2. Steady-state field distribution in a photonic crystal waveguide branch, at a frequency where nearly 100% transmission occurs. White circles indicate the positions of the dielectric cylinders. Plotted here is the amplitude of the electric field component that is parallel to the cylinders.

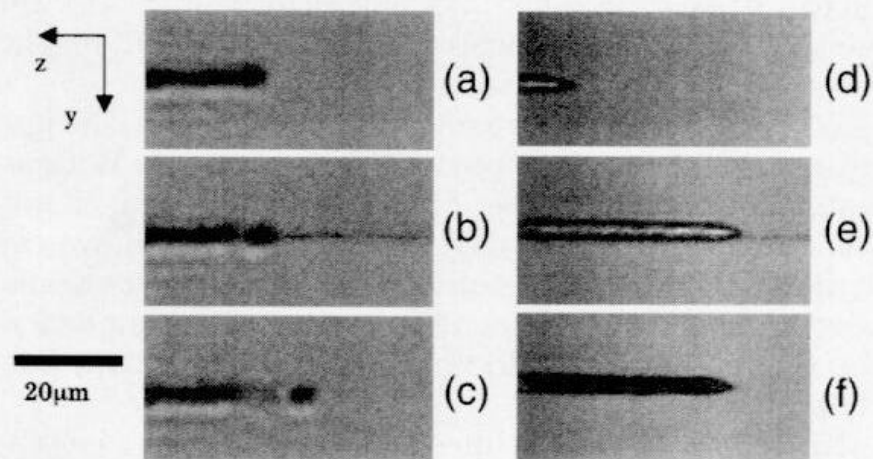


Fig. 2. Microdrilling of silica glass from its rear surface in air without and with an inflow of water into the hole. Incident energy, $1 \mu\text{J}$ per pulse. (a)–(c) Drilling without an inflow of water; (d), (e) drilling with an inflow of water. (f) Image of (e) after the water has receded.

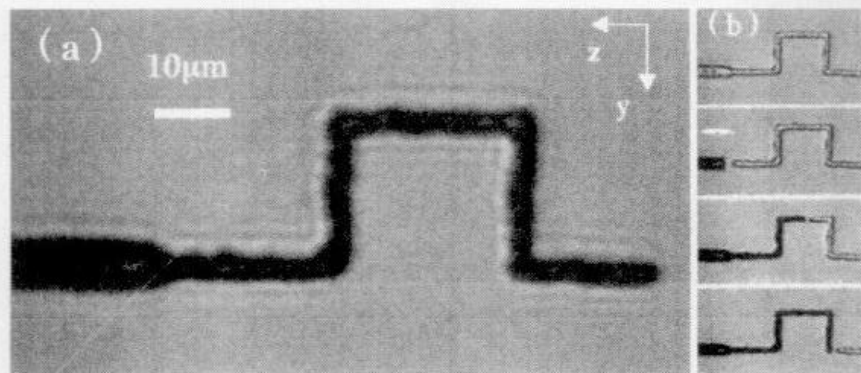


Fig. 4. Square-wave shaped hole drilled by movement of the sample in different directions. (a) The finished hole with diameters of $\sim 7 \mu\text{m}$ (pulse energy, $\sim 4 \mu\text{J}$) and $\sim 4 \mu\text{m}$ (pulse energy, $\sim 1 \mu\text{J}$). (b) Video clips of the drying process of the refilled hole.

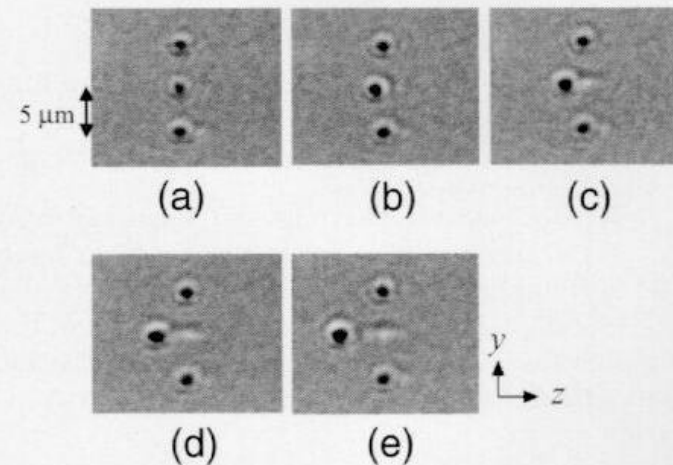


Fig. 2. (a)–(d) Side views of optical seizing and movement of a void. (e) Central void is moved toward the input plane by $5 \mu\text{m}$.

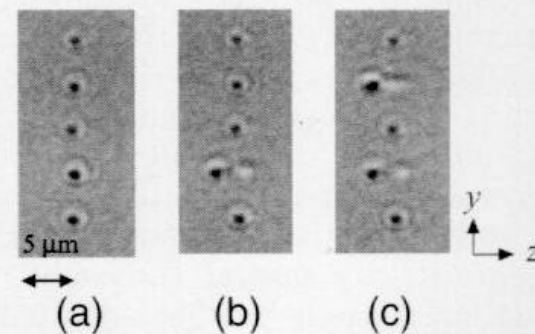


Fig. 3. Optical movement of arbitrary voids: (a) creation of voids, (b) movement of the fourth void, (c) movement of the second void.

Large-scale optical integration - in 3-D

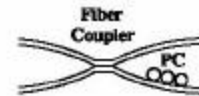
- high-density optical memory devices



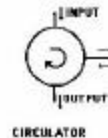
- waveguides - singlemode, multimode, hollow channels



- directional couplers, X-coupler



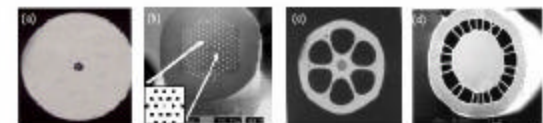
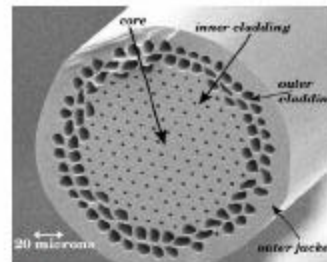
- circulators, fiber gratings, modulators



- photonic 2-D and 3-D crystals



- holey waveguides



Conclusions

- Potential to create large-scale optical integration in 3-D
- Re-writable optical components may be possible
- High precision micromachining of virtually all optical materials
- Potential to produce sub-micron, or nano-meter features